

2SC1636

Silicon NPN LEC Transistor

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- h_{FE} 500-2000
- $V_{BE} \geq 25V$
- $V_{CE(sat)} \leq 75mV$
- Industrial Use: 2SC1981⑤ (Can Type)

絶対最大定格 Absolute Maximum Ratings $T_a = 25^\circ C$

Characteristics		Symbol	2SC1636
Collector-to-Base Voltage	V_{CBO}	50 V	
Collector-to-Emitter Voltage	V_{CEO}	25 V	
Emitter-to-Base Voltage	V_{EBO}	25 V	
Collector Current	I_C	20 mA	
Emitter Current	I_E	-20 mA	
Collector Power Dissipation	P_C	300 mW	
Junction Temperature	T_j	120°C	
Storage Temperature	T^{stg}	-50+120°C	



電氣的特性 Electrical Characteristics $T_a = 25^\circ C$

Characteristics		Symbol	Conditions	Min.	Typ.	Max.	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 50V, I_E = 0$				0.2	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 25V, I_C = 0$				0.2	μA
Emitter-to-Base Voltage	V_{EBO}	$I_E = 0.1mA, I_C = 0$	25				V
Collector-to-Emitter Sustaining Voltage	$V_{CE(sus)}$	$I_C = 2mA$	25				V
Collector-to-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C = 10mA, I_B = 1mA$				75	mV
Base-to-Emitter Saturation Voltage	$V_{BE(sat)}$					0.8	V
DC Current Gain	h_{FE}	$I_C = 1mA, V_{CE} = 3V$	500		2000		
Gain Bandwidth Product	f_T	$V_{CE} = 6V, I_E = -2mA$	30				MHz
Output Capacitance	C_{ob}	$V_{CB} = 6V, I_E = 0, f = 1MHz$	4			7	pF
Noise Figure	NF	$I_C = 0.1mA, V_{CE} = 6V, f = 10Hz, R_g = 10k\Omega$	2				dB
Delay Time	t_d	$V_{CC} = 10V, I_C = 30mA$	30				ns
Rise Time	t_r		75				ns
Storage Time	t_{stg}	$I_{B1} = -I_{B2} = 3mA$	600				ns
Fall Time	t_f	Fig. 1	130				ns

